

660x660um Silicon PIN PD Chip datasheet

P/N : WS9H-01C

Application

Si PIN photodiode chip

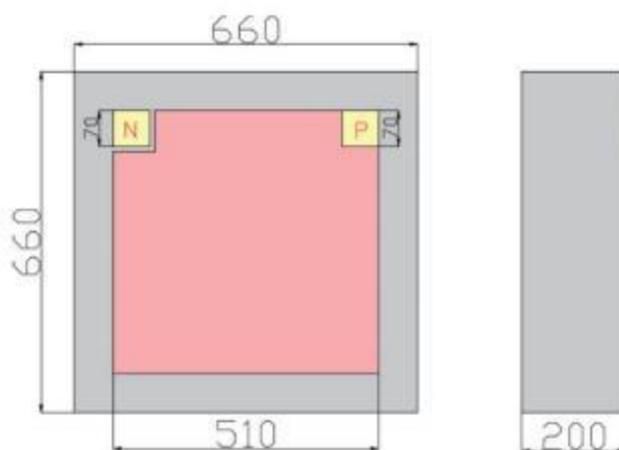
Structure

Planar type : PIN diode

Electrodes :

Top side (Cathode) : Al

Top side (Anode) : Al



DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	510 x 510±15			μm
Chip width	660±25			μm
Chip length	660±25			μm
Chip height	180	200	220	μm
Pad N(Cathode)	70			μm
Pad P(Anode)	70			μm

Electro-Optical Characteristics (@ Ta =25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=10mA, H =0	0.5		1.3	V
Reverse Voltage	V br	Ir =100μA, H =0	35			V
Reverse Dark Current	Id	Vr =10V			10	nA
Sensitive Wavelength Range	λp		400	940	1100	nm
Capacitance	Cj	VR =3V, f=1MHz		8		pF